

Skyrmions in a hole gas with large spin gap and strong disorder

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Acta Physica Polonica A **110**, 163 (2006)

Quantum Hall skyrmions in a hole gas with a large spin gap

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Characterization of nanocrystalline TiO₂-HfO₂ thin films prepared by low pressure hot target reactive magnetron sputtering

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Contactless electroreflectance spectroscopy of Ga(In)NAs/GaAs quantum well structures containing Sb atoms

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